



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	80V
I_D	100A

$R_{DS(ON)}$ P-AMCID 11/Lang (en-US)-BDC q0.00000 841.01W*0 0 1 517t0 G[A]TJETQq0.00000888 0 59



YJG100G08E

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	3.6	4.5	m
		$V_{GS}=4.5V, I_D=20A$	-	4.8	6.5	
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$	-	0.8	1.2	V
Maximum Body-Diode Continuous Current	I_S		-	-	100	A
Gate resistance	R_G	$f=1MHz$	-	2	-	

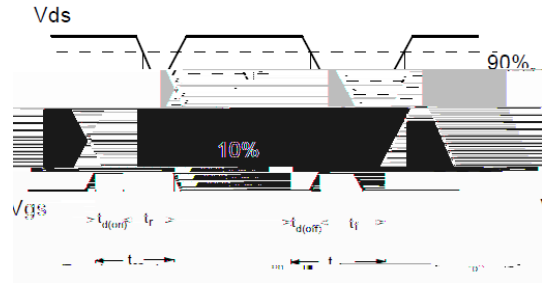
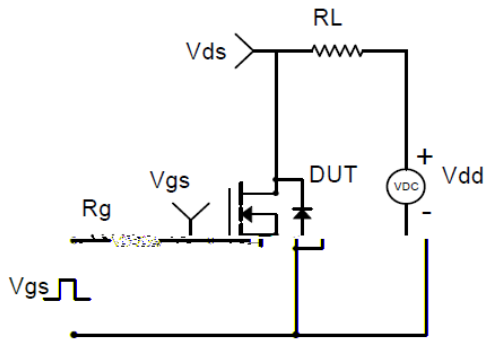
Transconductance (181.75 637.39 0.48 0.48 r



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Typical Performance Characteristic $T_f 0 0 1 \pm 0.5.1 T_m 0 g 0 G -0.08 T_c 10000 \mu JETQ EMC /P MCID$



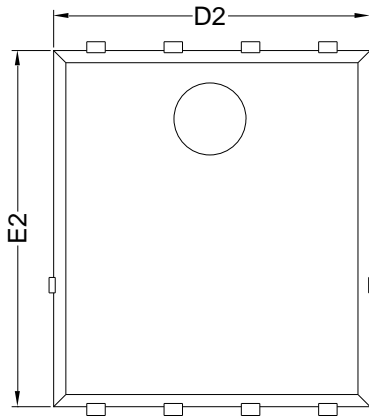


Resistive Switching Test Circuit &

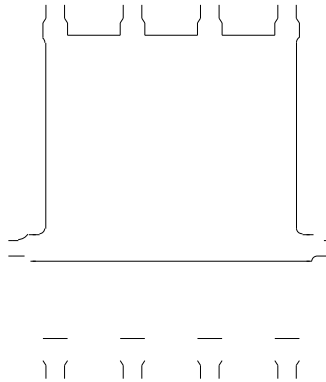


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PDFN5060-8L-B-1.1MM Package information



Top View



Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



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Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to hs (n)30()42(t)-10(o)30()-1d(i)-14(a)(si)a i rod()-1ce i rp7(d)3(o)3(cu)30(m)-34(e)30()-10(o)30()-1